## NSN 5961-00-136-4909

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Inclosure Material:
Metal
Overall Length:
0.520 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
0.890 inches
Thread Size:
0.312 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
120.0 collector to emitter voltage/static/base open and 125.0 collector to base voltage/static/emitter open and 6.0 emitter to base voltage,
static, collector open
Current Rating Per Characteristic:
20.00 amperes source cutoff current and 10.00 amperes source cutoff current
Power Rating Per Characteristic:
150.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
18876-mis-14150 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
3 tab, solder lug
Specification Data:
18876-mis-14150/49 government specification
Shelf Life:

N/a

**Unit Of Measure:** 

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No

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